

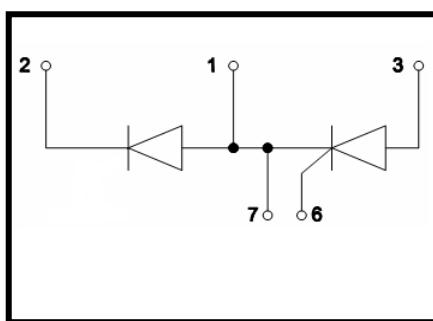
## Features

- Isolation Voltage 3000 V~
- Industrial Standard Package
- High Surge Capability
- Glass Passivated Chips
- Simple Mounting
- Electrically Isolated by DBC Ceramic



## Applications

- DC Motor Control and Drives
- Battery Charges
- Welders
- Power Converters
- Lighting Control
- Heat and Temperature Control



## Advantages

- Space and Weight Savings
- Improved Temperature and Power Cycling

### ■ Diode

## ABSOLUTE MAXIMUM RATINGS

 $T_C=25^\circ\text{C}$  unless otherwise specified

Symbol	Test Condition	Value	Unit
$V_{RRM}$		1600	V
$I_{d(AV)}$	$T_C=100^\circ\text{C}$ , module	160	A
$I_{FSM}$	$T_J=45^\circ\text{C}$ ; $t=10\text{ms}$ (50Hz), sine	5160	A
	$V_R=0$ $t=8.3\text{ms}$ (60Hz), sine	5420	A
$I^2t$	$T_J=45^\circ\text{C}$ ; $t=10\text{ms}$ (50Hz), sine	133.1	$\text{KA}^2\text{s}$
	$V_R=0$ $t=8.3\text{ms}$ (60Hz), sine	121.9	$\text{KA}^2\text{s}$
$T_J$	Junction Temperature	-40~150	$^\circ\text{C}$

## ELECTRICAL AND THERMAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

Symbol	Test Condition	Value	Unit
$I_R$	$V_R = V_{RRM}$ ; $T_J = 25^\circ\text{C}$	$\leq 0.5$	mA
	$V_R = V_{RRM}$ ; $T_J = T_{JM}$	$\leq 6$	mA
$V_F$	$I_F=500\text{A}$	1.50	V
$V_{TO}$	For power-loss calculations only	0.8	V
$R_{thJC}$	Thermal Resistance , Junction-to-Case	0.18	K/W
$R_{thCS}$	Thermal Resistance, Case -to-Sink	0.10	K/W

## ■ Thyristor

### ABSOLUTE MAXIMUM RATINGS

$T_C=25^\circ\text{C}$  unless otherwise specified

Symbol	Test Condition	Value	Unit
$V_{RRM}/V_{DRM}$		1600	V
$I_{T(AV)}$	$T_C=85^\circ\text{C}$ , 180° conduction, half sine wave;	160	A
$I_{T(RMS)}$	as AC switch;	355	A
$I_{TSM}$	$T_J=45^\circ\text{C}$ , $t=10\text{ms}$ (50Hz), sine, $V_R=0$ ;	3000	A
	$T_J=45^\circ\text{C}$ , $t=8.3\text{ ms}$ (60Hz), sine, $V_R=0$ ;	3200	
$I^2t$	$T_J=45^\circ\text{C}$ , $t=10\text{ms}$ (50Hz), sine, $V_R=0$ ;	45	$\text{KA}^2\text{s}$
	$T_J=45^\circ\text{C}$ , $t=8.3\text{ ms}$ (60Hz), sine, $V_R=0$ ;	42.5	
$I_{DRM}/I_{RRM}$	$V_R=V_{RRM}$ , $V_D=V_{DRM}$ , gate open circuit;	0.5	mA
	$T_J=125^\circ\text{C}$ , $V_R=V_{RRM}$ , $V_D=V_{DRM}$ , gate open circuit;	40	mA
$dV/dt$	$T_J=125^\circ\text{C}$ , exponential to 67% rated $V_{DRM}$	1000	V/us
$V_{ISOL}$	50Hz, all terminals shorted, $t=1\text{min}$ , $I_{ISOL}\leq 1\text{mA}$ ;	3000	V~
$T_J$	Max. junction operating temperature range	-40~125	°C
$T_{STG}$	Max. storage temperature range	-40~125	°C

### ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

Symbol	Test Condition	Min.	Typ.	Max.	Unit
$V_{TO}$	$16.7\% \times \pi \times I_{AV} < I < \pi \times I_{AV}$ , $T_J = 125^\circ\text{C}$ ;			0.80	V
	$I > \pi \times I_{AV}$ , $T_J = 125^\circ\text{C}$ ;			0.98	V
$r_t$	$16.7\% \times \pi \times I_{AV} < I < \pi \times I_{AV}$ , $T_J = 125^\circ\text{C}$ ;			1.67	$\text{m}\Omega$
	$I > \pi \times I_{AV}$ , $T_J = 125^\circ\text{C}$ ;			1.38	$\text{m}\Omega$
$I_H$	$V_{AK}=6\text{V}$ , initial $I_T=30\text{A}$ ;			200	mA
$I_L$	Anode supply =6V, resistive load=1Ω, gate pulse =10V, 100us;			400	mA
$V_{TM}$	$I_{TM}=500\text{A}$ , $t_d=10\text{ ms}$ , half sine;		1.54	2.0	V
$P_{GM}$	$t_p\leq 5\text{ms}$ , $T_j=125^\circ\text{C}$ ;			12	W
$P_{GM(AV)}$	$f=50\text{Hz}$ , $T_j=125^\circ\text{C}$ ;			3	W
$I_{GM}$ - $V_{GT}$				3	A
	$t_p\leq 5\text{ms}$ , $T_j=125^\circ\text{C}$ ;			10	V
$V_{GT}$	$V_A=6\text{V}$ , $R_A=1\Omega$ , $T_j=-40^\circ\text{C}$ ;			4	V
	$V_A=6\text{V}$ , $R_A=1\Omega$ ;			2.5	
	$V_A=6\text{V}$ , $R_A=1\Omega$ , $T_j=125^\circ\text{C}$ ;			1.7	
$I_{GT}$	$V_A=6\text{V}$ , $R_A=1\Omega$ , $T_j=-40^\circ\text{C}$ ;			270	mA
	$V_A=6\text{V}$ , $R_A=1\Omega$ ;			150	
	$V_A=6\text{V}$ , $R_A=1\Omega$ , $T_j=125^\circ\text{C}$ ;			80	
$V_{GD}$	$V_{AK}=V_{DRM}$ , $T_j=125^\circ\text{C}$			0.3	V
$I_{GD}$				10	mA
$di/dt$	$I_{TM}=400\text{A}$ , rated $V_{DRM}$ , $T_j=125^\circ\text{C}$			300	A/us

**THERMAL AND MECHANICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

<b>Symbol</b>	<b>Test Condition</b>	<b>value</b>	<b>Unit</b>
$R_{\text{thjc}}$	DC operation, per junction;	0.18	K/W
$R_{\text{THCS}}$	Mounting surface smooth, flat and greased, per junction;	0.1	K/W
$M_d$	Mounting torque(M6)	3 ~ 5	N·m
	Terminal connection torque(M6)		
Weight	Typical value	156	g

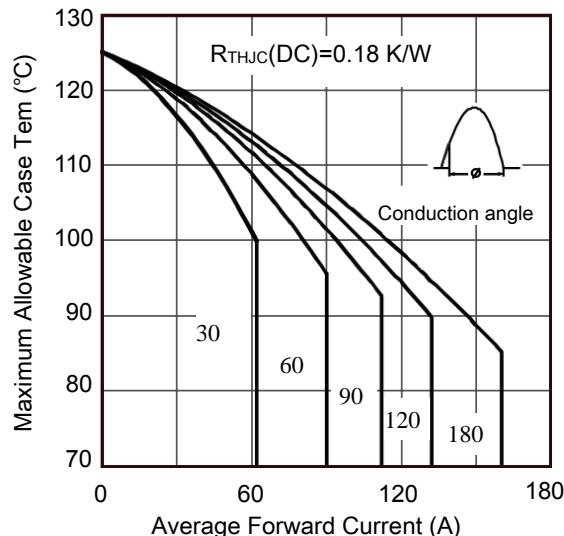
**Characteristic curves**

Figure 1. Current Rating Characteristics

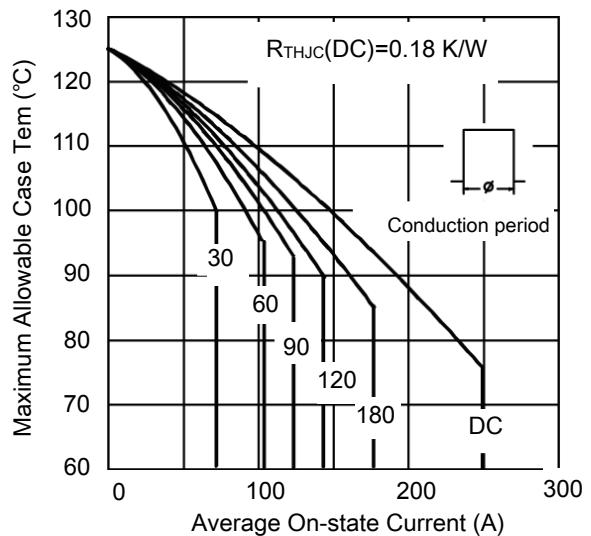


Figure 2. Current Rating Characteristics

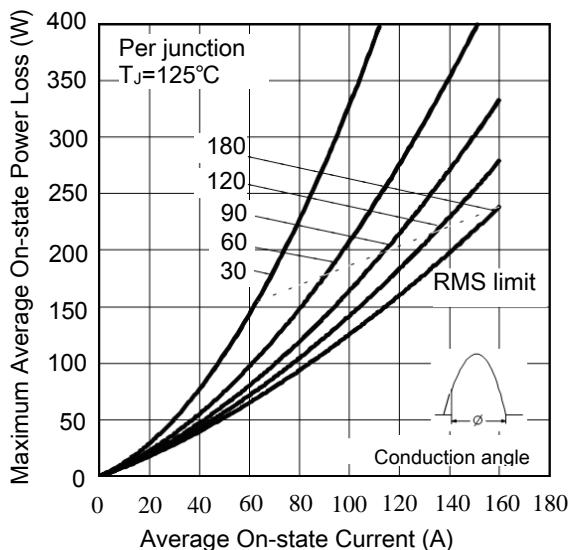


Figure 3. On-state Power Loss Characteristics

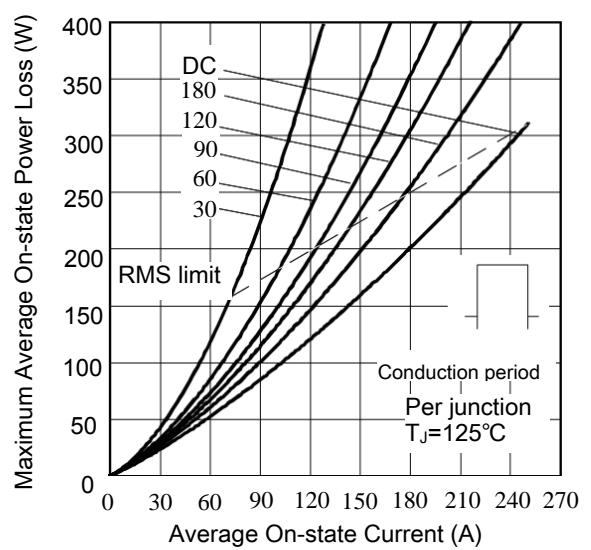


Figure 4. On-state Power Loss Characteristics

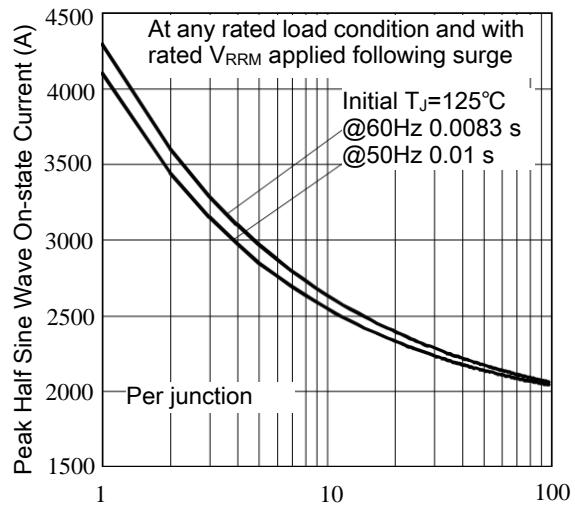


Figure 5. Maximum Non-Repetitive Surge Current

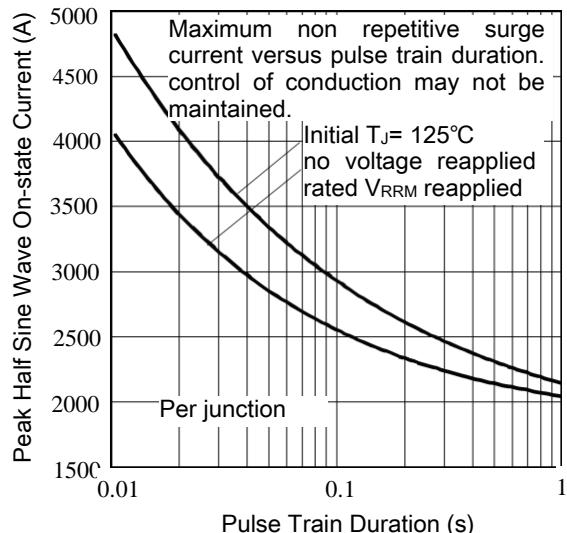


Figure 6. Maximum Non-Repetitive Surge Current

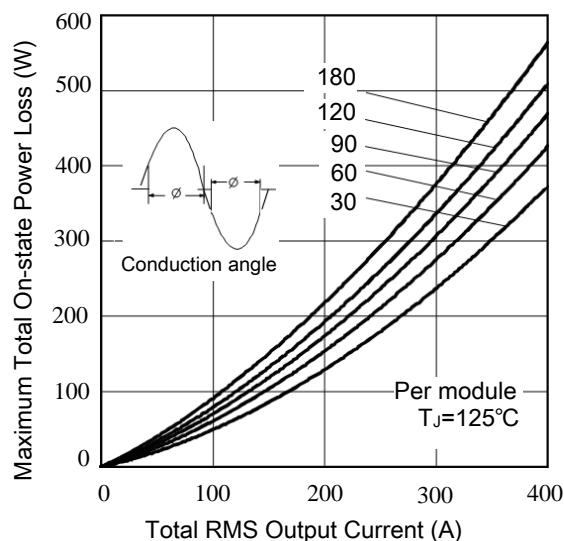


Figure 7. On-State Power Loss Characteristics-1

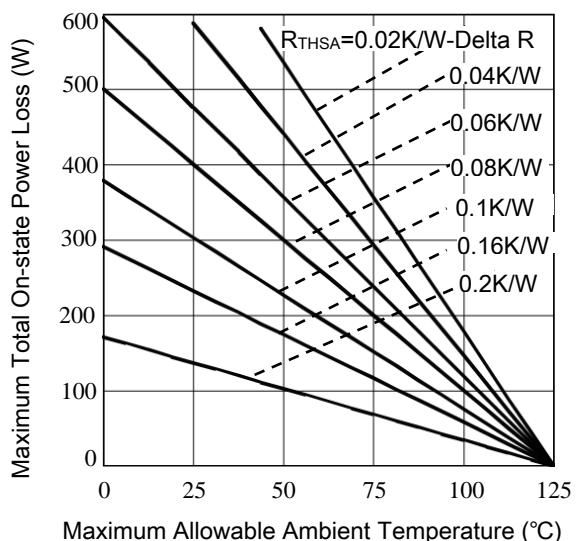


Figure 8 On-State Power Loss Characteristics-2

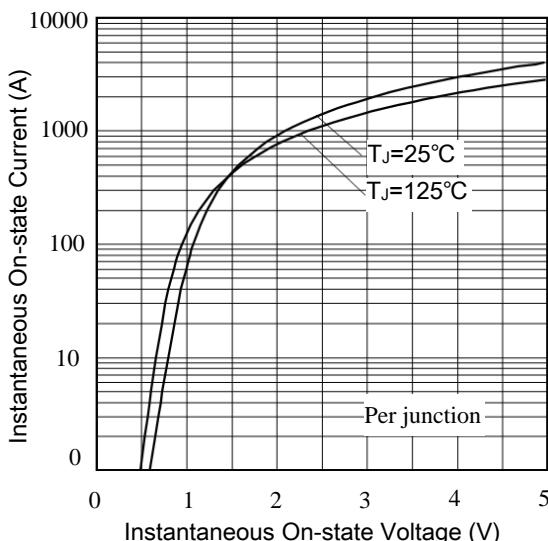


Figure 9. On State Voltage Drop Characteristics

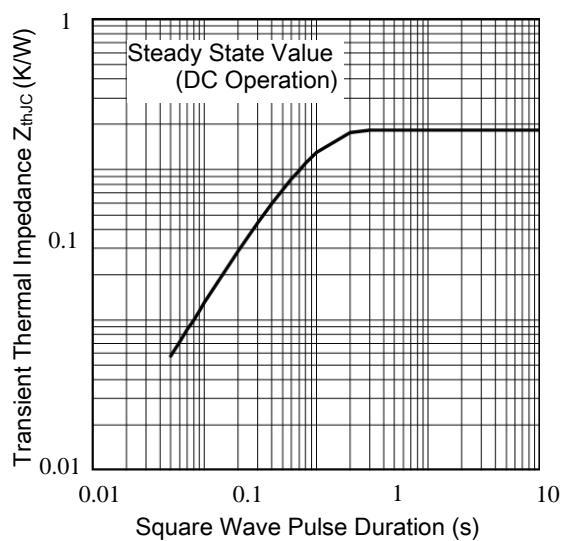


Figure 10. Thermal Impedance  $Z_{thJC}$  Characteristics

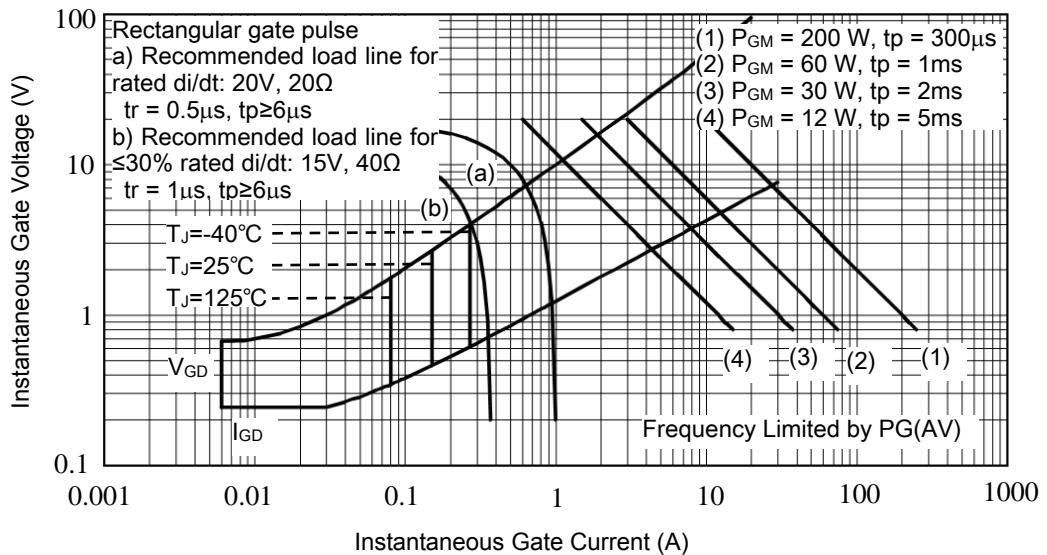


Figure 11. Gate Characteristics

**Package Outline (Dimensions in mm)**